

Alexey Novikov

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

172
papers

1,075
citations

16
h-index

23
g-index

189
ext. papers

1,230
ext. citations





1.7
avg, IF

3.89
L-index

#	Paper	IF	Citations
172	Influence of irradiation by Swift Heavy Ions (SHI) on electronic magnetotransport in Sb layer in silicon. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2022 , 138, 115047	3	0
171	Luminescent properties of spatially ordered Ge/Si quantum dots epitaxially grown on a pit-patterned silicon-on-insulator substrate. <i>Journal of Luminescence</i> , 2022 , 249, 119033	3.8	1
170	Formation and Optical Properties of Locally Strained Ge Microstructures Embedded into Cavities. <i>Semiconductors</i> , 2021 , 55, 531	0.7	
169	Near-infrared stimulated emission from indium-rich InGaN layers grown by plasma-assisted MBE. <i>Applied Physics Letters</i> , 2021 , 118, 151902	3.4	1
168	One-Stage Formation of Two-Dimensional Photonic Crystal and Spatially Ordered Arrays of Self-Assembled Ge(Si) Nanoislands on Pit-Patterned Silicon-On-Insulator Substrate. <i>Nanomaterials</i> , 2021 , 11,	5.4	3
167	Photonic Bound States in the Continuum in Si Structures with the Self-Assembled Ge Nanoislands. <i>Laser and Photonics Reviews</i> , 2021 , 15, 2000242	8.3	8
166	Coupling of Germanium Quantum Dots with Collective Sub-radiant Modes of Silicon Nanopillar Arrays. <i>ACS Photonics</i> , 2021 , 8, 209-217	6.3	4
165	Mercury (II) Ion Detection using AgNWs-MoS ₂ Nanocomposite on GaN HEMT for IoT Enabled Smart Water Quality Analysis. <i>IEEE Internet of Things Journal</i> , 2021 , 1-1	10.7	2
164	Spin pump induced inverse spin Hall effect observed in Bi-doped n-type Si. <i>Physical Review B</i> , 2020 , 101,	3.3	2
163	Impact of Ge deposition temperature on parameters of c-Si solar cells with surface texture formed by etching of Si using SiGe islands as a mask. <i>Materials Science in Semiconductor Processing</i> , 2020 , 114, 105065	4.3	3
162	Influence of the Growth Conditions and Doping Level on the Luminescence Kinetics of Ge:Sb Layers Grown on Silicon. <i>Semiconductors</i> , 2020 , 54, 811-816	0.7	0
161	Effect of antimony doping on the energy of optical transitions in n-Ge layers grown on Si (001) and Ge (001) substrates. <i>Journal of Applied Physics</i> , 2020 , 127, 165701	2.5	0
160	Ultrasensitive Detection of Mercury Ions Under UV Illumination of MoS ₂ Functionalized AlGaIn/GaN Transistor. <i>IEEE Transactions on Electron Devices</i> , 2020 , 67, 5693-5700	2.9	3
159	Kinetics of the Luminescence Response of Self-Assembled Ge(Si) Nanoislands Embedded in Two-Dimensional Photonic Crystals. <i>Semiconductors</i> , 2020 , 54, 1352-1359	0.7	0
158	Luminescence of Spatially Ordered Self-Assembled Solitary Ge(Si) Nanoislands and their Groups Incorporated into Photonic Crystals. <i>Semiconductors</i> , 2020 , 54, 853-859	0.7	4
157	Enhancement of the Luminescence Signal from Self-Assembled Ge(Si) Nanoislands due to Interaction with the Modes of Two-Dimensional Photonic Crystals. <i>Semiconductors</i> , 2020 , 54, 975-981	0.7	0
156	Acoustic properties of strained SiGe/Si layers in the sub-terahertz frequency range. <i>Journal of Applied Physics</i> , 2020 , 127, 154304	2.5	0

155	Comparative Analysis of the Luminescence of Ge:Sb Layers Grown on Ge(001) and Si(001) Substrates. <i>Semiconductors</i> , 2019 , 53, 1318-1323	0.7	1
154	Locally Strained Ge/SOI Structures with an Improved Heat Sink as an Active Medium for Silicon Optoelectronics. <i>Semiconductors</i> , 2019 , 53, 1324-1328	0.7	1
153	Impact of size distributions of Ge islands as etching masks for anisotropic etching on formation of anti-reflection structures. <i>Japanese Journal of Applied Physics</i> , 2019 , 58, 045505	1.4	8
152	Influence of Annealing on the Properties of Ge:Sb/Si(001) Layers with an Antimony Concentration Above Its Equilibrium Solubility in Germanium. <i>Semiconductors</i> , 2019 , 53, 882-886	0.7	3
151	Emission Properties of Heavily Doped Epitaxial Indium-Nitride Layers. <i>Semiconductors</i> , 2019 , 53, 1357-1362	0.7	2
150	Ordered Arrays of Ge(Si) Quantum Dots Incorporated into Two-Dimensional Photonic Crystals. <i>Semiconductors</i> , 2019 , 53, 1329-1333	0.7	4
149	Pulsed Ion-Beam Treatment of Germanium Implanted by Antimony Ions. <i>Optoelectronics, Instrumentation and Data Processing</i> , 2019 , 55, 423-430	0.6	1
148	Light emission from Ge(Si)/SOI self-assembled nanoislands embedded in photonic crystal slabs of various periods with and without cavities. <i>Semiconductor Science and Technology</i> , 2019 , 34, 024003	1.8	12
147	Visible Luminescence of SiGe/Si Quantum Wells Under an External Anisotropic Deformation. <i>Journal of Russian Laser Research</i> , 2018 , 39, 83-89	0.7	
146	Strain-Induced Intrinsic Splitting of the Biexciton Ground State in SiGe/Si Quantum Wells. <i>Journal of Russian Laser Research</i> , 2018 , 39, 90-94	0.7	
145	Structural and electrical properties of Ge-on-Si(0 0 1) layers with ultra heavy n-type doping grown by MBE. <i>Journal of Crystal Growth</i> , 2018 , 491, 26-30	1.6	9
144	Towards the indium nitride laser: obtaining infrared stimulated emission from planar monocrystalline InN structures. <i>Scientific Reports</i> , 2018 , 8, 9454	4.9	15
143	MOCVD Growth of InGaAs/GaAs/AlGaAs Laser Structures with Quantum Wells on Ge/Si Substrates. <i>Crystals</i> , 2018 , 8, 311	2.3	9
142	Study of the Structural and Emission Properties of Ge(Si) Quantum Dots Ordered on the Si(001) Surface. <i>Semiconductors</i> , 2018 , 52, 1150-1155	0.7	5
141	Formation of light-trapping structure using Ge islands grown by gas-source molecular beam epitaxy as etching masks. <i>Japanese Journal of Applied Physics</i> , 2018 , 57, 08RB04	1.4	2
140	Observation of strained SiGe nanoislands embedded in a Si matrix using ambient cross-sectional atomic force microscopy 2018 , 123-126		
139	Formation of black silicon using SiGe self-assembled islands as a mask for selective anisotropic etching of silicon. <i>Materials Science in Semiconductor Processing</i> , 2018 , 75, 143-148	4.3	9
138	Fabrication of light-trapping structure by selective etching of thin Si substrates masked with a Ge dot layer and nanomasks. <i>Japanese Journal of Applied Physics</i> , 2018 , 57, 08RF09	1.4	3

137	On the Application of Strain-Compensating GaAsP Layers for the Growth of InGaAs/GaAs Quantum-Well Laser Heterostructures Emitting at Wavelengths above 1100 nm on Artificial Ge/Si Substrates. <i>Semiconductors</i> , 2018 , 52, 1547-1550	0.7	3
136	Influence of thermal annealing on the electrical and luminescent properties of heavily Sb-doped Ge/Si(001) layers. <i>Semiconductor Science and Technology</i> , 2018 , 33, 124019	1.8	6
135	Visible Emission from a Dense Biexciton Gas in SiGe/Si Quantum Wells under External Anisotropic Strain. <i>JETP Letters</i> , 2018 , 107, 358-363	1.2	
134	A New Limitation of the Depth Resolution in TOF-SIMS Elemental Profiling: the Influence of a Probing Ion Beam. <i>Technical Physics Letters</i> , 2018 , 44, 320-323	0.7	1
133	Stimulated Emission in the 1.3–1.5 μm Spectral Range from AlGaInAs Quantum Wells in Hybrid Light-Emitting III-V Heterostructures on Silicon Substrates. <i>Semiconductors</i> , 2018 , 52, 1495-1499	0.7	
132	Formation and Properties of Locally Tensile Strained Ge Microstructures for Silicon Photonics. <i>Semiconductors</i> , 2018 , 52, 1442-1447	0.7	2
131	Stimulated Emission at 1.3- μm Wavelength in Metamorphic InGaAs/InGaAsP Structure with Quantum Wells Grown on Ge/Si(001) Substrate. <i>Technical Physics Letters</i> , 2018 , 44, 735-738	0.7	
130	Heating and evaporation of a two-dimensional electron-hole liquid by heat pulses. <i>JETP Letters</i> , 2017 , 105, 179-184	1.2	1
129	Phase transitions in a two-dimensional system of dipolar excitons in a double-well SiGe/Si heterostructure. <i>Bulletin of the Russian Academy of Sciences: Physics</i> , 2017 , 81, 341-344	0.4	
128	On the stimulated emission of InGaAs/GaAs/AlGaAs laser structures grown by MOCVD on exact and inclined Ge/Si(001) substrates. <i>Semiconductors</i> , 2017 , 51, 663-666	0.7	5
127	Quantum Dot Emission Driven by Mie Resonances in Silicon Nanostructures. <i>Nano Letters</i> , 2017 , 17, 6886-6892	1.6	8
126	Antimony segregation and n-type doping in Si/Si(111) films grown by molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 2017 , 475, 291-294	1.6	
125	Specific features of the photoexcitation spectra of epitaxial InN layers grown by molecular-beam epitaxy with the plasma activation of nitrogen. <i>Semiconductors</i> , 2017 , 51, 1537-1541	0.7	
124	Selective etching of Si, SiGe, Ge and its usage for increasing the efficiency of silicon solar cells. <i>Semiconductors</i> , 2017 , 51, 1542-1546	0.7	7
123	Antimony segregation in Si layers grown by molecular beam epitaxy on Si wafers with different crystallographic orientations. <i>Semiconductors</i> , 2017 , 51, 1552-1556	0.7	
122	Technology of the production of laser diodes based on GaAs/InGaAs/AlGaAs structures grown on a Ge/Si substrate. <i>Semiconductors</i> , 2017 , 51, 1477-1480	0.7	4
121	Peculiarities of growing InGaAs/GaAs/AlGaAs laser structures by MOCVD on Ge/Si substrates. <i>Semiconductors</i> , 2017 , 51, 1527-1530	0.7	5
120	Electrically pumped InGaAs/GaAs quantum well microdisk lasers directly grown on Si(100) with Ge/GaAs buffer. <i>Optics Express</i> , 2017 , 25, 16754-16760	3.3	12

119	Magnetotransport in Si langleSb rangle Delta-Layer after Swift Heavy Ion-Induced Modification. <i>Acta Physica Polonica A</i> , 2017 , 132, 229-232	0.6	2
118	  Ge/Si(001). <i>Fizika I Tekhnika Poluprovodnikov</i> , 2017 , 51, 695	0	
117	 Ge/Si <i>Fizika I Tekhnika Poluprovodnikov</i> , 2017 , 51, 1530	0	
116	 Ge/Si. <i>Fizika I Tekhnika Poluprovodnikov</i> , 2017 , 51, 1579	0	
115	Epitaxial GaN layers formed on langasite substrates by the plasma-assisted MBE method. <i>Semiconductors</i> , 2016 , 50, 1511-1514	0.7	0
114	Electroluminescence from MIS silicon-based light emitters with arrays of self-assembled Ge(Si) nanoislands. <i>Semiconductors</i> , 2016 , 50, 1475-1478	0.7	
113	Fine structure of the emission spectrum of a two-dimensional electronhole liquid in SiGe/Si quantum wells. <i>JETP Letters</i> , 2016 , 104, 163-168	1.2	9
112	Plasmonic enhancement of four-particle radiative recombination in SiGe quantum wells. <i>JETP Letters</i> , 2016 , 104, 231-235	1.2	2
111	Electroluminescence of structures with self-assembled Ge(Si) nanoislands confined between strained Si layers. <i>Semiconductors</i> , 2016 , 50, 1657-1661	0.7	
110	On the radiative recombination and tunneling of charge carriers in SiGe/Si heterostructures with double quantum wells. <i>Semiconductors</i> , 2016 , 50, 1604-1608	0.7	
109			
108	Monolithically integrated InGaAs/GaAs/AlGaAs quantum well laser grown by MOCVD on exact Ge/Si(001) substrate. <i>Applied Physics Letters</i> , 2016 , 109, 061111	3.4	19
107	Influence of surface roughness on a change in the growth mode from two-dimensional to three-dimensional for strained SiGe heterostructures. <i>Semiconductors</i> , 2016 , 50, 1630-1634	0.7	1
106	Nonlinear calibration curves in secondary ion mass spectrometry for quantitative analysis of gesi heterostructures with nanoclusters. <i>Technical Physics Letters</i> , 2016 , 42, 243-247	0.7	2
105	Features of SOI substrates heating in MBE growth process obtained by low-coherence tandem interferometry. <i>Journal of Crystal Growth</i> , 2016 , 448, 89-92	1.6	1
104	Features of InN growth by nitrogen-plasma-assisted MBE at different ratios of fluxes of group-III and -V elements. <i>Semiconductors</i> , 2016 , 50, 261-265	0.7	4
103	Quantitative depth profiling of Si _{1-x} Gex structures by time-of-flight secondary ion mass spectrometry and secondary neutral mass spectrometry. <i>Thin Solid Films</i> , 2016 , 607, 25-31	2.2	5
102	Plastic relaxation in GeSi layers on Si (001) and Si (115) substrates. <i>Semiconductors</i> , 2015 , 49, 19-22	0.7	

101	Influence of Boron Selective Doping on the Edge Luminescence of SiGe/Si Quantum Wells. <i>Journal of Russian Laser Research</i> , 2015 , 36, 66-73	0.7	
100	Hodographs in diode-structure diagnostics. <i>Semiconductors</i> , 2015 , 49, 1443-1447	0.7	
99	Impact of growth and annealing conditions on the parameters of Ge/Si(001) relaxed layers grown by molecular beam epitaxy. <i>Semiconductors</i> , 2015 , 49, 1415-1420	0.7	18
98	The waveguide effect of InGaAs quantum wells in a GaAs structure on Si substrate with Ge buffer layer. <i>Technical Physics Letters</i> , 2015 , 41, 648-650	0.7	2
97	Growth of light-emitting SiGe heterostructures on strained silicon-on-insulator substrates with a thin oxide layer. <i>Semiconductors</i> , 2015 , 49, 1104-1110	0.7	3
96	Antimony segregation in Ge and formation of n-type selectively doped Ge films in molecular beam epitaxy. <i>Journal of Applied Physics</i> , 2015 , 118, 145701	2.5	19
95	Control of surface dip diameter in Si-based photonic nanostructures by changing growth temperature of Ge quantum dot multilayer structures and its impact on their optical properties. <i>Japanese Journal of Applied Physics</i> , 2015 , 54, 08KA01	1.4	4
94	Multiparticle states and the factors that complicate an experimental observation of the quantum coherence in the exciton gas of SiGe/Si quantum wells. <i>Journal of Experimental and Theoretical Physics</i> , 2015 , 121, 1052-1066	1	9
93	Segregation of Sb in Ge epitaxial layers and its usage for the selective doping of Ge-based structures. <i>Semiconductors</i> , 2015 , 49, 1405-1409	0.7	2
92	Excitation spectra of photoluminescence and its kinetics in structures with self-assembled Ge:Si nanoislands. <i>Semiconductors</i> , 2015 , 49, 1410-1414	0.7	4
91	Excitonic luminescence of SiGe/Si quantum wells doped with boron. <i>Journal of Applied Physics</i> , 2015 , 117, 185705	2.5	6
90	Real-time measurement of substrate temperature in molecular beam epitaxy using low-coherence tandem interferometry. <i>Journal of Crystal Growth</i> , 2015 , 413, 42-45	1.6	8
89	Quantitative calibration and germanium SIMS depth profiling in Ge x Si1-x /Si heterostructures. <i>Semiconductors</i> , 2014 , 48, 1109-1117	0.7	5
88	A new approach to the diagnostics of nanoislands in Ge x Si1-x /Si heterostructures by secondary ion mass spectrometry. <i>Technical Physics Letters</i> , 2014 , 40, 601-605	0.7	7
87	Use of related parameters in X-ray diffraction analysis of multilayer structures with allowance for the layer growth time. <i>Technical Physics</i> , 2014 , 59, 402-406	0.5	3
86	Investigation of deformations and strain fields in silicon matrix structures embedded with vertically stacked Ge(Si) self-assembled islands. <i>Applied Physics Letters</i> , 2014 , 105, 161910	3.4	1
85	Coulomb centers assisted tunneling in a doped triple barrier SiGe heterostructure. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2014 , 57, 42-46	3	
84	Segregation of Sb in SiGe heterostructures grown by molecular beam epitaxy: Interdependence of growth conditions and structure parameters. <i>Journal of Crystal Growth</i> , 2014 , 396, 66-70	1.6	7

83	Transition from the two- to three-dimensional growth of Ge films upon deposition onto relaxed SiGe/Si(001) buffer layers. <i>Semiconductors</i> , 2013 , 47, 427-432	0.7	3
82	Dynamics of the phase transitions in the system of nonequilibrium charge carriers in quantum-dimensional Si _{1-x} Ge _x /Si structures. <i>Journal of Experimental and Theoretical Physics</i> , 2013 , 117, 912-925	1	14
81	Antimony segregation in stressed SiGe heterostructures grown by molecular beam epitaxy. <i>Semiconductors</i> , 2013 , 47, 1481-1484	0.7	1
80	Time-resolved photoluminescence from self-assembled Ge(Si) islands in multilayer SiGe/Si and SiGe/SOI structures. <i>Semiconductors</i> , 2013 , 47, 1496-1499	0.7	5
79	Sb mediated formation of Ge/Si quantum dots: Growth and properties. <i>Thin Solid Films</i> , 2012 , 520, 3322-3325		8
78	New approach to the X-ray diffraction analysis of test structures during flow calibration in epitaxial growth reactors. <i>Journal of Surface Investigation</i> , 2012 , 6, 494-497	0.5	2
77	Layer-by-layer analysis of structures containing δ layers by secondary ion mass spectrometry taking into account the TOF.SIMS-5 depth resolution function. <i>Journal of Surface Investigation</i> , 2012 , 6, 574-577	0.5	2
76	Photoluminescence excitation spectroscopy technique modified for studying structures with self-assembled Ge(Si)/Si(001) nanoislands. <i>Technical Physics Letters</i> , 2012 , 38, 828-831	0.7	2
75	Barrier-height modification in Schottky silicon diodes with highly doped 3D and 2D layers. <i>Semiconductors</i> , 2012 , 46, 1358-1361	0.7	6
74	Optical monitoring of technological parameters during molecular-beam epitaxy. <i>Semiconductors</i> , 2012 , 46, 1471-1475	0.7	18
73	Method for taking into account the shift parameter in the deconvolution of the depth composition distribution of semiconductor structures from SIMS depth profiles. <i>Semiconductors</i> , 2012 , 46, 1481-1486	0.7	5
72	Effect of silicon spacer thickness on the electroluminescence of multilayer structures with self-assembled Ge(Si)/Si(001) islands. <i>Semiconductors</i> , 2012 , 46, 1418-1422	0.7	4
71	Effects of the lateral ordering of self-assembled SiGe nanoislands grown on strained Si _{1-x} Ge _x buffer layers. <i>Semiconductors</i> , 2012 , 46, 647-654	0.7	4
70	Transition from planar to island growth mode in SiGe structures fabricated on SiGe/Si(001) strain-relaxed buffers. <i>Applied Physics Letters</i> , 2012 , 101, 151601	3.4	5
69	SiGe nanostructures with self-assembled islands for Si-based optoelectronics. <i>Semiconductor Science and Technology</i> , 2011 , 26, 014029	1.8	25
68	Usage of antimony segregation for selective doping of Si in molecular beam epitaxy. <i>Journal of Applied Physics</i> , 2011 , 109, 113533	2.5	17
67	Condensation of excitons and the spectrum of multiparticle states in SiGe/Si quantum wells: The role of the barrier in the conduction band. <i>JETP Letters</i> , 2011 , 94, 63-67	1.2	23
66	Method of selective doping of silicon by segregating impurities. <i>Technical Physics Letters</i> , 2011 , 37, 824-826		1

65	TOF-SIMS 5 instrument sensitivity to matrix elements in GeSi Layers: Analysis based on recording of complex secondary ions. <i>Journal of Surface Investigation</i> , 2011 , 5, 591-594	0.5	9
64	Comparative analysis of radiation effects on the electroluminescence of Si and SiGe/Si(001) heterostructures with self-assembled Islands. <i>Semiconductors</i> , 2011 , 45, 225-229	0.7	9
63	Photoluminescence line width of self-assembled Ge(Si) islands arranged between strained Si layers. <i>Semiconductors</i> , 2011 , 45, 198-202	0.7	10
62	Direct comparison of superlattice periods measured with X-ray diffractometry and optical interferometry. <i>Bulletin of the Russian Academy of Sciences: Physics</i> , 2011 , 75, 40-43	0.4	2
61	Narrow photoluminescence peak from Ge(Si) islands embedded between tensile-strained Si layers. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011 , 8, 1055-1059		
60	Electron-hole liquid and excitonic molecules in quasi-two-dimensional SiGe layers of Si/SiGe/Si heterostructures. <i>JETP Letters</i> , 2010 , 92, 305-309	1.2	17
59	Gigantic uphill diffusion during self-assembled growth of Ge quantum dots on strained SiGe sublayers. <i>Applied Physics Letters</i> , 2010 , 96, 141909	3.4	16
58	Observation of the electron-hole liquid in Si _{1-x} Ge _x /Si quantum wells by steady-state and time-resolved photoluminescence measurements. <i>Physical Review B</i> , 2010 , 82,	3.3	35
57	Effect of irradiation on the luminescence properties of low-dimensional SiGe/Si(001) heterostructures. <i>Semiconductors</i> , 2010 , 44, 329-334	0.7	12
56	Secondary cluster ions Ge ₂ ⁺ and Ge ₃ ⁺ for improving depth resolution of SIMS depth profiling of GeSi/Si heterostructures. <i>Semiconductors</i> , 2010 , 44, 401-404	0.7	9
55	Study of the transition of the epitaxial Ge film from layer-to-layer to three-dimensional growth in heterostructures with strained SiGe sublayers. <i>Semiconductors</i> , 2010 , 44, 519-524	0.7	2
54	Distinctions in the Ge wetting layer formation and self-assembled island nucleation between single- and multilayer SiGe/Si(0 0 1) structures. <i>Journal of Crystal Growth</i> , 2010 , 313, 12-15	1.6	
53	Comparative analysis of photoluminescence and electroluminescence of multilayer structures with self-assembled Ge(Si)/Si(001) island 2010 , 42, 286		
52	Effects of boron and phosphorus doping on the photoluminescence of self-assembled germanium quantum dots. <i>Applied Physics Letters</i> , 2009 , 94, 183103	3.4	9
51	Features of two-dimensional to three-dimensional growth mode transition of Ge in SiGe/Si(001) heterostructures with strained layers. <i>Applied Physics Letters</i> , 2009 , 95, 151902	3.4	12
50	Electroluminescence and photoconductivity of GeSi heterostructures with self-assembled islands in the wavelength range 1.31-1.55 μ m. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2009 , 41, 935-938	3	9
49	Phase transitions in nonequilibrium electron-hole systems of Si/SiGe/Si nanoheterostructures. <i>Bulletin of the Russian Academy of Sciences: Physics</i> , 2009 , 73, 70-72	0.4	
48	Influence of elastic strains in sublayers on the critical thickness of the Stranski-Krastanow transition for the GeSi/Si(001) system. <i>Journal of Surface Investigation</i> , 2009 , 3, 548-553	0.5	6

47	Distribution of germanium in Si _{1-x} Ge _x (x Journal of Experimental and Theoretical Physics, 2009 , 109, 997-1010	1	6
46	Effect of parameters of Ge(Si)/Si(001) self-assembled islands on their electroluminescence at room temperature. <i>Semiconductors</i> , 2009 , 43, 313-317	0.7	10
45	Exciton condensation in the compressively strained SiGe layers of Si/SiGe/Si heterostructures. <i>Thin Solid Films</i> , 2008 , 517, 55-56	2.2	4
44	Effect of growth temperature on photoluminescence of Ge(Si) self-assembled islands embedded in a tensile-strained Si layer. <i>Thin Solid Films</i> , 2008 , 517, 385-387	2.2	
43	Cooperative effects in SiGe/Si quantum wells. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2008 , 40, 1172-1174	3	10
42	Comparative analysis of photo- and electroluminescence of multilayer structures with Ge(Si)/Si(001) self-assembled islands. <i>Thin Solid Films</i> , 2008 , 517, 398-400	2.2	3
41	Radiation hardness of GeSi heterostructures with thin Ge layers. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2008 , 147, 191-194	3.1	7
40	Channels of radiative recombination and phase transitions in a system of nonequilibrium carriers in a Si _{0.93} Ge _{0.07} /Si thin quantum well. <i>Journal of Experimental and Theoretical Physics</i> , 2008 , 107, 846-853 ¹		14
39	Comparative analysis of photoluminescence and electroluminescence of multilayer structures with self-assembled Ge(Si)/Si(001) island. <i>Semiconductors</i> , 2008 , 42, 286-290	0.7	10
38	Photoluminescence of dome and hut shaped Ge(Si) self-assembled islands embedded in a tensile-strained Si layer. <i>Applied Physics Letters</i> , 2007 , 91, 021916	3.4	10
37	Effect of tensile-strained Si layer on photoluminescence of Ge(Si) self-assembled islands grown on relaxed SiGe/Si(001) buffer layers. <i>Semiconductors</i> , 2007 , 41, 167-171	0.7	3
36	Effect of growth temperature on photoluminescence of self-assembled Ge(Si) islands confined between strained Si layers. <i>Semiconductors</i> , 2007 , 41, 1356-1360	0.7	3
35	Intense photoluminescence from Ge(Si) self-assembled islands embedded in a tensile-strained Si layer. <i>Semiconductor Science and Technology</i> , 2007 , 22, S29-S32	1.8	8
34	The effect of local atomic structure on the optical properties of GeSi self-assembled islands buried in silicon matrix. <i>Nanotechnology</i> , 2007 , 18, 115711	3.4	13
33	Photoluminescence of Ge(Si) self-assembled islands embedded in a tensile-strained Si layer. <i>Applied Physics Letters</i> , 2006 , 88, 011914	3.4	14
32	Special features of the formation of Ge(Si) islands on the relaxed Si _{1-x} Ge _x /Si(001) buffer layers. <i>Semiconductors</i> , 2006 , 40, 229-233	0.7	5
31	Special features of the photoluminescence of self-assembled Ge(Si)/Si(001) islands grown on a strained Si _{1-x} Ge _x layer. <i>Semiconductors</i> , 2006 , 40, 338-341	0.7	
30	Experimental and theoretical study of the influence of growth temperature on composition in self-assembled SiGe QD's. <i>Materials Science and Engineering C</i> , 2005 , 25, 565-569	8.3	2

29	Growth and photoluminescence of self-assembled islands obtained during the deposition of Ge on a strained SiGe layer. <i>Optical Materials</i> , 2005 , 27, 818-821	3.3	31
28	Influence of a predeposited Si _{1-x} Ge _x layer on the growth of self-assembled SiGe/Si(001) islands. <i>Physics of the Solid State</i> , 2005 , 47, 26	0.8	8
27	Influence of the germanium deposition rate on the growth and Photoluminescence of Ge(Si)/Si(001) self-assembled islands. <i>Physics of the Solid State</i> , 2005 , 47, 38	0.8	4
26	Si _{1-x} Ge _x /Si(001) relaxed buffer layers grown by chemical vapor deposition at atmospheric pressure. <i>Physics of the Solid State</i> , 2005 , 47, 42	0.8	8
25	Negative photoconductivity of selectively doped SiGe/Si: B heterostructures with a two-dimensional hole gas in the middle-infrared range. <i>Physics of the Solid State</i> , 2005 , 47, 46	0.8	1
24	Raman spectroscopy and electroreflectance studies of self-assembled SiGe nanoislands grown at various temperatures. <i>Physics of the Solid State</i> , 2005 , 47, 54	0.8	18
23	Ge self-assembled islands grown on SiGe/Si(001) relaxed buffer layers. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2005 , 124-125, 466-469	3.1	4
22	Fabrication of Strain-Relaxed Si _{1-x} Ge _x /Si(001) Buffer Layers of Low Surface Roughness. <i>Russian Microelectronics</i> , 2005 , 34, 203-209	0.5	5
21	GeSi/Si(001) Structures with Self-Assembled Islands: Growth and Optical Properties 2005 , 333-351		2
20	Photoluminescence of self-assembled GeSi/Si(001) nanoislands of different shapes. <i>Physics of the Solid State</i> , 2004 , 46, 60-63	0.8	8
19	Correlation between the energy of SiGe nanoislands and their shape and size. <i>Physics of the Solid State</i> , 2004 , 46, 67-70	0.8	
18	Composition and elastic stresses in multilayer structures with Si _{1-x} Ge _x nanoislands. <i>Physics of the Solid State</i> , 2004 , 46, 85-88	0.8	1
17	Phonons in Ge/Si quantum dot structures: influence of growth temperature. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2004 , 21, 464-468	3	12
16	Photoluminescence of GeSi/Si(0 0 1) self-assembled islands with dome and hut shape. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2004 , 23, 416-420	3	6
15	Visualization of buried SiGe quantum dots at cleavages by cross-sectional atomic force microscopy. <i>Applied Physics Letters</i> , 2004 , 85, 1999-2001	3.4	1
14	HRTEM study of growth-correlated properties of (Si,Ge) islands. <i>Microscopy and Microanalysis</i> , 2003 , 9, 220-221	0.5	
13	Theoretical and experimental investigations of single- and multilayer structures with SiGe nanoislands. <i>Materials Science and Engineering C</i> , 2003 , 23, 1027-1031	8.3	14
12	Impurity photoconductivity in SiGe/Si:B multi-quantum-well heterostructures. <i>Physica B: Condensed Matter</i> , 2003 , 340-342, 1065-1068	2.8	2

11	Photoluminescence of Ge(Si)/Si(0 0 1) self-assembled islands in the near infra-red wavelength range. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2003 , 16, 467-472	3	7
10	Atomic-force-microscopy visualization of GeSi buried nanoislands on crystal cleavages in silicon structures. <i>Semiconductors</i> , 2003 , 37, 667-674	0.7	2
9	Strain-driven alloying: effect on sizes, shape and photoluminescence of GeSi/Si(001) self-assembled islands. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2002 , 89, 62-65	2.1	16
8	Low-energy photoluminescence of structures with GeSi/Si(001) self-assembled nanoislands. <i>JETP Letters</i> , 2002 , 76, 365-369	1.2	18
7	Microscopic and optical investigation of Ge nanoislands on silicon substrates. <i>Nanotechnology</i> , 2002 , 13, 81-85	3.4	40
6	Effect of Si diffusion on growth of GeSi self-assembled islands. <i>Springer Proceedings in Physics</i> , 2001 , 377-378	0.2	
5	Transition from dome to pyramid shape of self-assembled GeSi islands. <i>Journal of Crystal Growth</i> , 2000 , 209, 302-305	1.6	11
4	The elastic strain and composition of self-assembled GeSi islands on Si(001). <i>Thin Solid Films</i> , 2000 , 367, 171-175	2.2	13
3	Shallow acceptors in Ge/GeSi multi-quantum well heterostructures. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2000 , 7, 608-611	3	4
2	Elastic strain and composition of self-assembled GeSi nanoislands on Si(001). <i>Semiconductors</i> , 2000 , 34, 6-10	0.7	3
1	Self-organization of germanium nanoislands obtained in silicon by molecular-beam epitaxy. <i>JETP Letters</i> , 1998 , 67, 48-53	1.2	27